

## MOSFET chip DMOST056-01

### Description

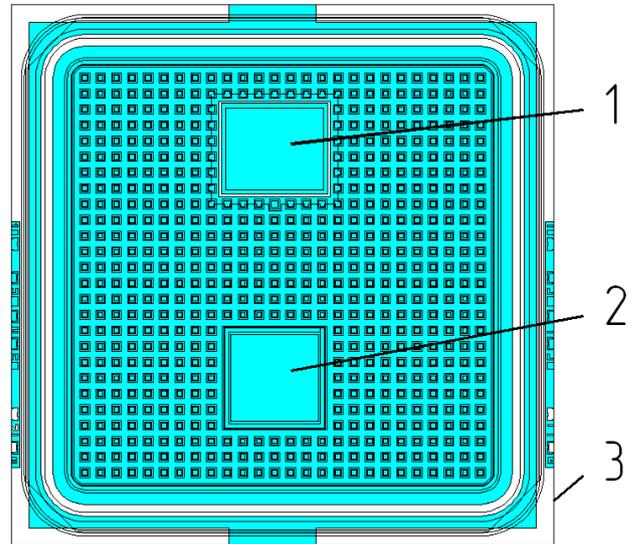
MOSFET chip with induced channel (normally-off)  
DMOST056-01 is designed to be used in hybrid  
microchips and packaged field-effect transistors.

### Features

- Chip size – 1.37 x1.37 mm
- Chip thickness – 0.42±0.02 mm
- Contact pads size:  
Gate – 0.248 x0.208 mm  
Source – 0.221 x 0.221 mm
- Metallization: top – AlSi,  
bottom – CrAu for bonding on conductive  
adhesive

### Absolute Maximum Ratings

Maximum Temperature	
Storage Temperature	- 60 °C to 100 °C
Operating Junction Temperature	- 45 °C to 85 °C
Maximum Voltage	
Drain-to-Source Voltage	230 V
Gate-to-Source Voltage	±20 V



- 1 - Gate  
2 - Source  
3 - Drain

### Electrical Characteristics ( $T_A = 25\text{ °C}$ )

Parameter	Symbol	Unit	Min.	Typ.	Max.	Conditions
Drain-to-Source ON-State Resistance	$R_{DS}$	Ohm			7.0	$V_{GS} = 5\text{ V}$ , $I_D = 150\text{ mA}$
Gate Leakage Current	$I_{LEAK.G}$	$\mu\text{A}$			0.1	$V_{GS} = \pm 20\text{ V}$ , $V_{DS} = 0\text{ V}$
Drain Leakage Current	$I_{LEAK.D}$	$\mu\text{A}$			1	$V_{GS} = 0\text{ V}$ , $V_D = 230\text{ V}$
LED Constant Forward Voltage (drain <sup>-</sup> , source <sup>+</sup> )	$V_{SD}$	V			0.95	$V_{GS} = 0\text{ V}$ , $I_S = 120\text{ mA}$